General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT–323/SC–70 package which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board T _A = 25°C	P _D	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	280	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

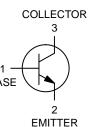


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SC-70 CASE 419 STYLE 3



MARKING DIAGRAM



P1 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device		Package	Shipping [†]
MMBT2222AWT	1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBT2222AW	T1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure. BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charact	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS				•	
Collector – Emitter Breakdown Voltage (No $(I_C = 10 \text{ mAdc}, I_B = 0)$	ote 1)	V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc$, $I_E = 0$)		V _{(BR)CBO}	75	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current $(V_{CE} = 60 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc})$		I _{BL}	-	20	nAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	_	10	nAdc
ON CHARACTERISTICS (Note 1)		•		•	
		H _{FE}	35 50 75 100 40	- - 300 -	-
Collector – Emitter Saturation Voltage (Not ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	e 1)	V _{CE(sat)}	<u>-</u>	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)		V _{BE(sat)}	0.6	1.2 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					•
Current-Gain - Bandwidth Product (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 M	lHz)	f _T	300	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	30	pF
Input Impedance ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$	łz)	h _{ie}	0.25	1.25	kΩ
Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$	łz)	h _{re}	-	4.0	X 10 ⁻⁴
Small – Signal Current Gain (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)			75	375	_
Output Admittance ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)			25	200	μmhos
Noise Figure ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 100 \mu\text{Adc}$, $R_{S} = 1.0 \mu\text{Adc}$	$k\Omega$, $f = 1.0 \text{ kHz}$	NF	_	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	-	10	
Rise Time	$I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t _r	-	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t _s	_	225	ns
Fall Time $I_{B1} = I_{B2} = 15 \text{ mAdc}$			_	60	110

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

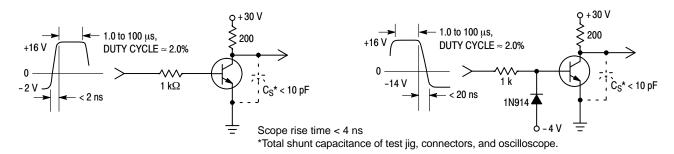


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

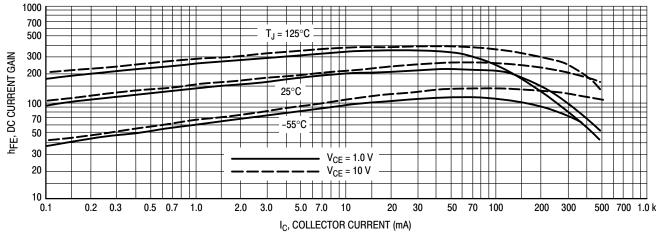


Figure 3. DC Current Gain

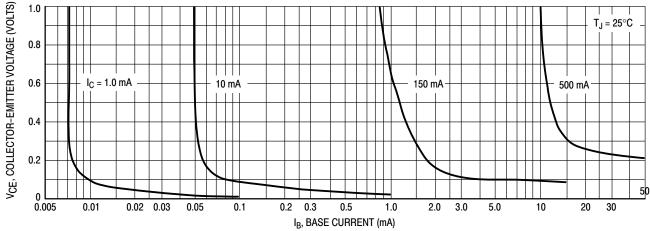


Figure 4. Collector Saturation Region

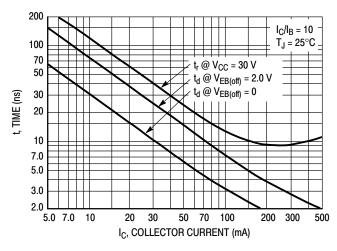


Figure 5. Turn - On Time

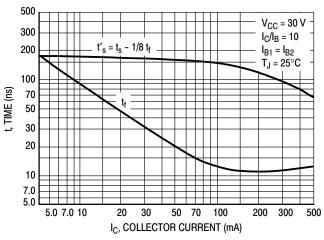


Figure 6. Turn-Off Time

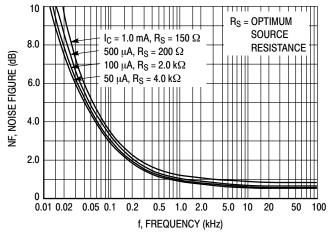


Figure 7. Frequency Effects

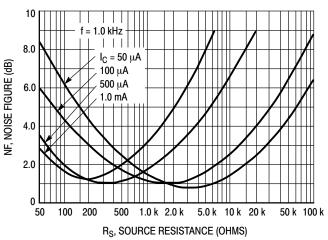


Figure 8. Source Resistance Effects

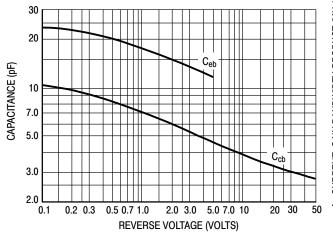


Figure 9. Capacitances

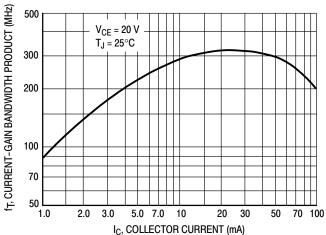


Figure 10. Current-Gain Bandwidth Product

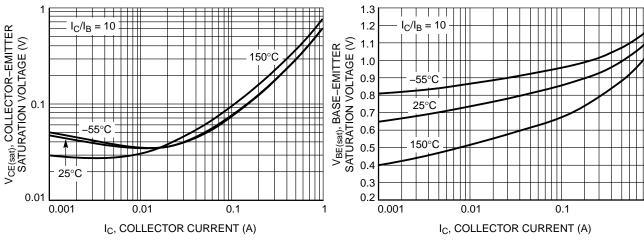


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current



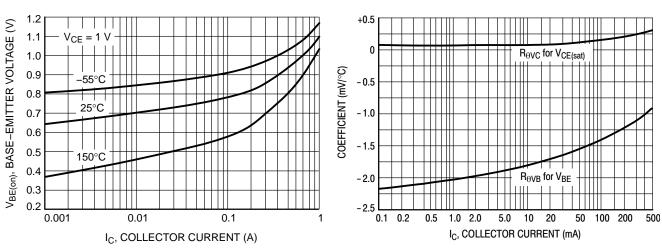


Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

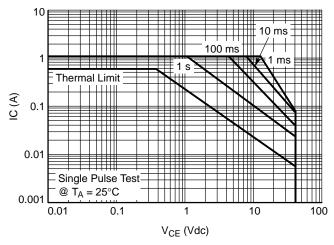


Figure 15. Safe Operating Area



SC-70 (SOT-323) CASE 419-04 ISSUE N

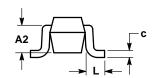
DATE 11 NOV 2008

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS		MILLIMETERS INCHE		INCHES	
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	=
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC	;	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

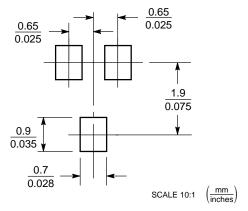
0.05 (0.002)

 H_{E}



SOLDERING FOOTPRINT*

е1



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XX= Specific Device Code Μ = Date Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	

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98ASB42819	В

PAGE 2 OF 2

ISSUE	REVISION	DATE
M	ADDED NOMINAL VALUES AND UPDATED GENERIC MARKING DIAGRAM. REQ. BY HONG XIAO	27 MAY 2005
N	CHANGED DIMENSION L VALUES TO 0.20, 0.38, 0.56 MM & 0.008, 0.015, 0.022 INCH. REQ. BY D. TRUHITTE.	11 NOV 2008

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